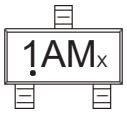
MMBT3904 TRANSISTOR (NPN)

SOT-23-3

FEATURES

- Complementary to MMBT3906

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)



1AM= Device code
Solid dot = Green molding compound device, if none, the normal device.
X= Code

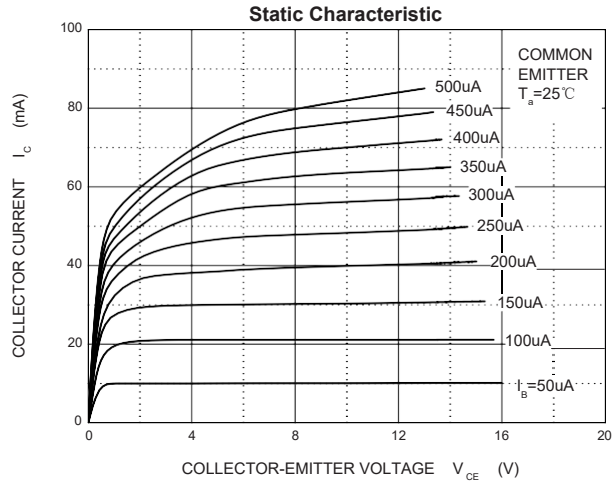
Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current	200	mA
P_C	Collector Power Dissipation	200	mW
$R_{\Theta JA}$	Thermal Resistance From Junction To Ambient	625	℃/W
T_J,T_{stg}	Operation Junction and Storage Temperature Range	-55～+150	℃

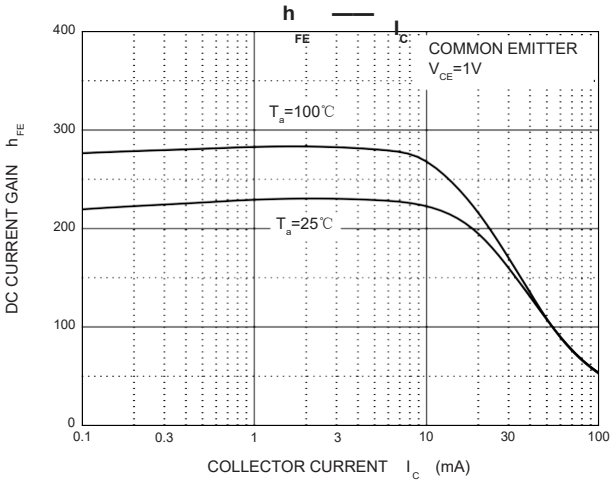
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

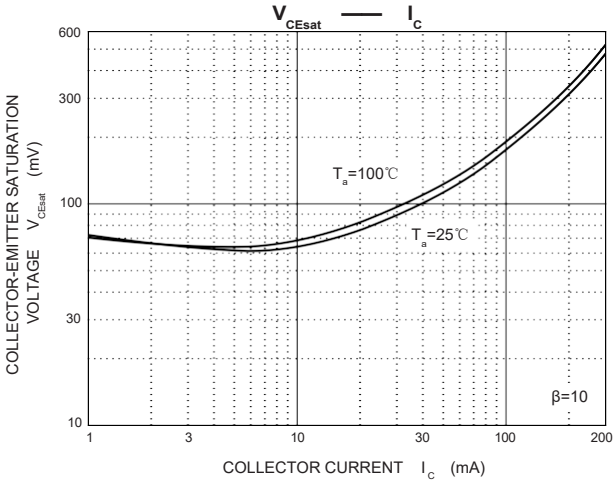
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA, I_E=0	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	6			V
Collector cut-off current	I_{CEX}	V_{CE}=30V, $V_{EB(off)}$=3V			50	nA
Collector cut-off current	I_{CBO}	V_{CB}= 60V, I_E=0			100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0			100	nA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C=10mA	100		300	
	$h_{FE(2)}$	V_{CE}=1V, I_C=50mA	60			
	$h_{FE(3)}$	V_{CE}=1V, I_C=100mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=50mA, I_B=5mA			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=50mA, I_B=5mA			0.95	V
Transition frequency	f_T	V_{CE}=20V,I_C=10mA, f=100MHz	300			MHz
Delay time	t_d	V_{CC}=3V, $V_{BE(off)}$=-0.5V I_C=10mA, I_{B1}=1mA			35	ns
Rise time	t_r	V_{CC}=3V, $V_{BE(off)}$=-0.5V I_C=10mA, I_{B1}=1mA			35	ns
Storage time	t_s	V_{CC}=3V, I_C=10mA, I_{B1}= I_{B2}=1mA			200	ns
Fall time	t_f	V_{CC}=3V, I_C=10mA, I_{B1}= I_{B2}=1mA			50	ns

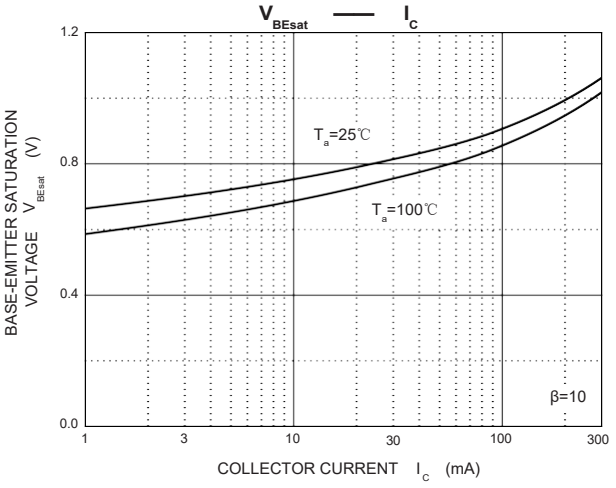
CLASSIFICATION OF $h_{FE(1)}$

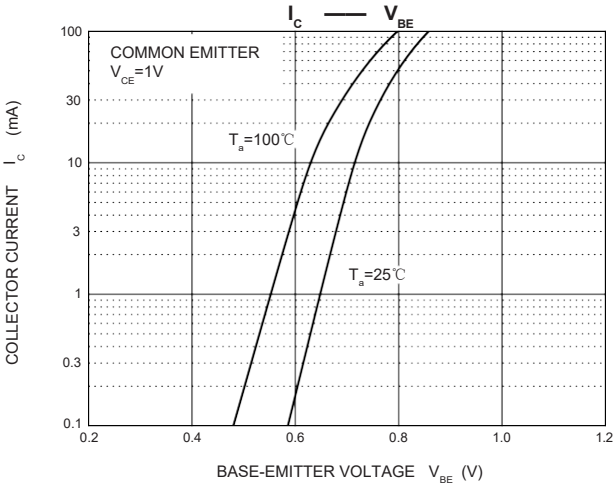
HFE	100-300	
RANK	L	H
RANGE	100－200	200－300

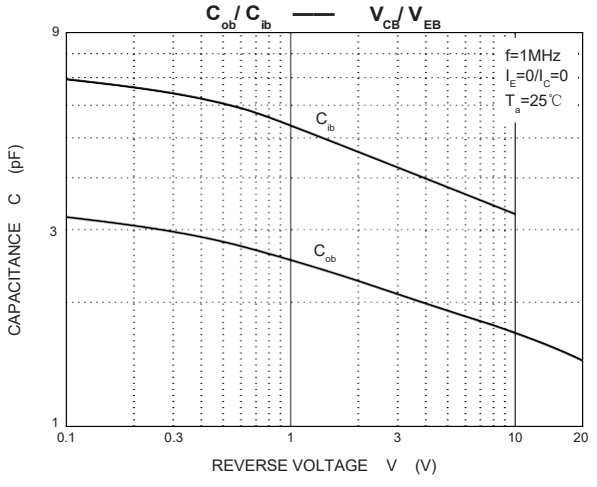

Static Characteristic
COMMON EMITTER
T_a=25℃
500uA
450uA
400uA
350uA
300uA
250uA
200uA
150uA
100uA
I_B=50uA
COLLECTOR CURRENT I_C (mA)
COLLECTOR-EMITTER VOLTAGE V_{CE} (V)

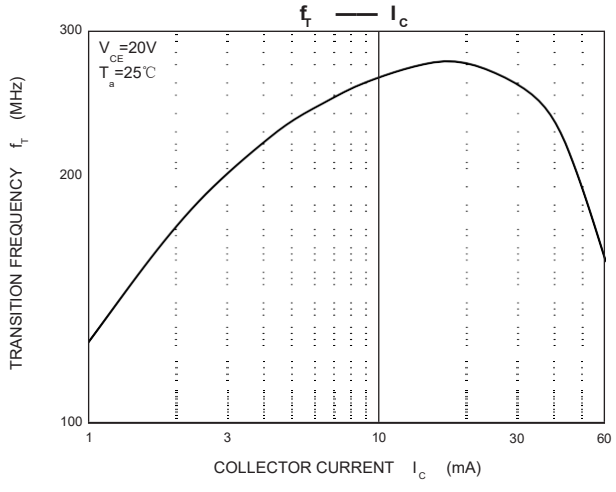

h_{FE} — I_C
COMMON EMITTER
V_{CE}=1V
T_a=100℃
T_a=25℃
DC CURRENT GAIN h_{FE}
COLLECTOR CURRENT I_C (mA)

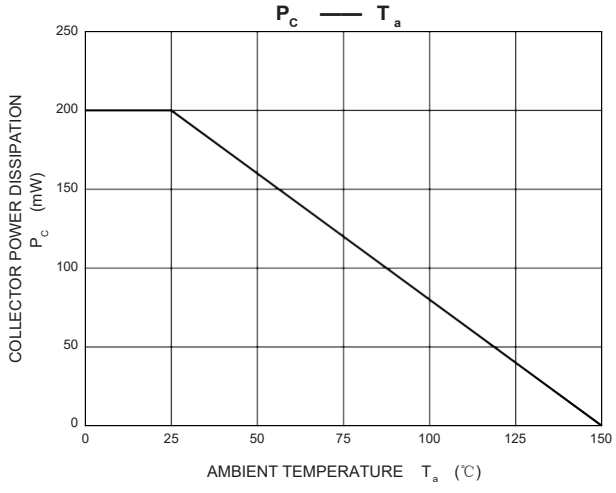

V_{CEsat} — I_C
T_a=100℃
T_a=25℃
β=10
COLLECTOR-EMITTER SATURATION VOLTAGE V_{CEsat} (mV)
COLLECTOR CURRENT I_C (mA)


V_{BEsat} — I_C
T_a=25℃
T_a=100℃
β=10
BASE-EMITTER SATURATION VOLTAGE V_{BEsat} (V)
COLLECTOR CURRENT I_C (mA)


I_C — V_{BE}
COMMON EMITTER
V_{CE}=1V
T_a=100℃
T_a=25℃
COLLECTOR CURRENT I_C (mA)
BASE-EMITTER VOLTAGE V_{BE} (V)


C_{ob} / C_{ib} — V_{CB} / V_{EB}
f=1MHz
I_E=0/I_C=0
T_a=25℃
C_{ib}
C_{ob}
CAPACITANCE C (pF)
REVERSE VOLTAGE V (V)


f_T — I_C
V_{CE}=20V
T_a=25℃
TRANSITION FREQUENCY f_T (MHz)
COLLECTOR CURRENT I_C (mA)


P_C — T_a
COLLECTOR POWER DISSIPATION P_C (mW)
AMBIENT TEMPERATURE T_a (℃)